# 2SC1567, 2SC1567A

#### Silicon NPN epitaxial planar type

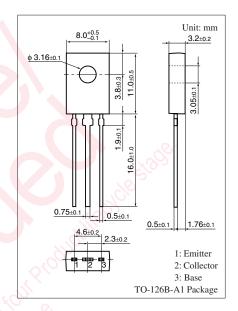
For low-frequency high power driver Complementary to 2SA0794, 2SA0794A

#### ■ Features

- ullet High collector-emitter voltage (Base open)  $V_{CEO}$
- Optimum for the driver stage of low-frequency and 40 W to 100 W output amplifier
- TO-126B package which requires no insulation plate for installation to the heat sink

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

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Parameter	Symbol	Rating	Unit			
Collector-base voltage	2SC1567	$V_{CBO}$	100	V		
(Emitter open)	2SC1567A		120			
Collector-emitter voltage	2SC1567	V <sub>CEO</sub>	100	V		
(Base open)	2SC1567A		120			
Emitter-base voltage (Coll	V <sub>EBO</sub>	5	V			
Collector current	I <sub>C</sub>	0.5	A			
Peak collector current	$I_{CP}$	1	A			
Collector power dissipation	P <sub>C</sub>	1.2	S W			
Junction temperature	$T_{j}$	150	°C			
Storage temperature	$T_{\rm stg}$	-55 to +150	°C			



### ■ Electrical Characteristics T<sub>a</sub> = 25°C ± 3°C

Parameter	- ~ (	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SC1567	V <sub>CEO</sub>	$I_C = 100 \mu\text{A},  I_B = 0$	100			V
(Base open)	2SC1567A		will soll	120			
Emitter-base voltage (Colle	ctor open)	$V_{EBO}$	$I_E = 1 \mu A, I_C = 0$	5			V
Forward current transfer ratio		h <sub>FE1</sub> *	$V_{CE} = 10 \text{ V}, I_{C} = 150 \text{ mA}$	130		330	_
		h <sub>FE2</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 500 \text{ mA}$	50	100		
Collector-emitter saturation	voltage	V <sub>CE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.2	0.4	V
Base-emitter saturation volt	age	V <sub>BE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.85	1.20	V
Transition frequency		$f_T$	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance		C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		11	20	pF
(Common base, input open	circuited)						

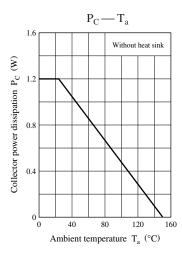
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

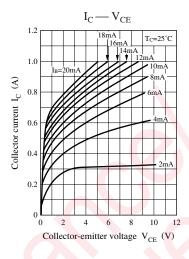
#### 2. \*: Rank classification

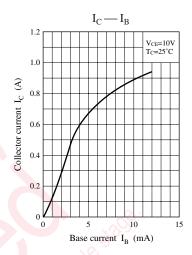
Rank	R	S
h <sub>FE1</sub>	130 to 220	185 to 330

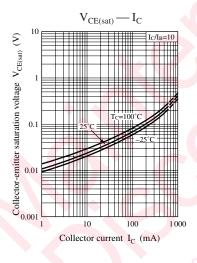
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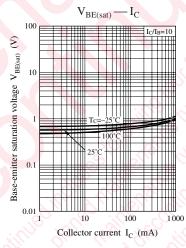
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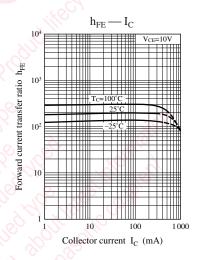


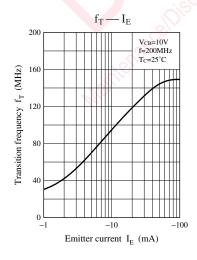


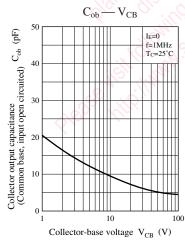


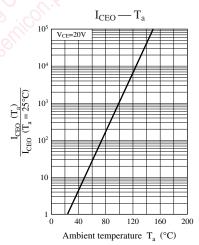






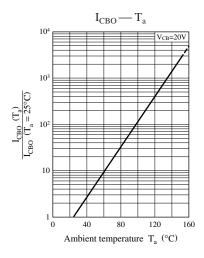


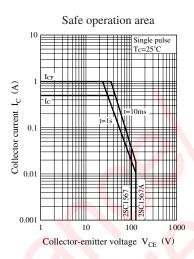




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